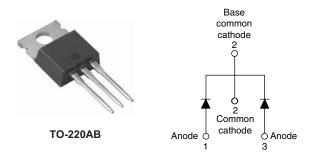


Vishay Semiconductors

Hyperfast Rectifier, 2 x 15 A FRED Pt®



PRODUCT SUMMARY						
Package	TO-220AB					
I _{F(AV)}	2 x 15 A					
V_R	300 V					
V _F at I _F	1.25 V					
t _{rr} typ.	See Recovery table					
T _J max.	175 °C					
Diode variation	Common cathode					

FEATURES

- · Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Compliant to RoHS Directive 2002/95/EC
- AEC-Q101 qualified





RoHS

DESCRIPTION/APPLICATIONS

300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diodes in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Peak repetitive reverse voltage		V_{RRM}		300	V		
Average rectified forward current	per diode	I _{F(AV)}	T _C = 153 °C	15	A		
	per device			30			
Non-repetitive peak surge current		I _{FSM}	T _C = 25 °C	150			
Operating junction and storage temp	peratures	T _J , T _{Stg}		- 65 to 175	°C		

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	300	-	-		
Forward voltage	V _F	I _F = 15 A	-	1.0	1.25	V	
		I _F = 15 A, T _J = 125 °C	-	0.85	0.95		
Reverse leakage current I _R		$V_R = V_R$ rated	-	-	40		
		$T_J = 125 ^{\circ}\text{C}, V_R = V_R \text{ rated}$	-	8	200	μΑ	
Junction capacitance	C _T	V _R = 300 V	-	38	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH	

VS-30CTH03PbF

Vishay Semiconductors Hyperfast Rectifier, 2 x 15 A FRED Pt®



DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time	t _{rr}	$I_F = 1 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	-	36		
		$I_F = 1 \text{ A, } dI_F/dt = 100 \text{ A/}\mu\text{s, } V_R = 30 \text{ V}$			-	30		
		T _J = 25 °C	$I_F = 15 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	33	-	ns	
		T _J = 125 °C		-	48	-		
Peak recovery current		T _J = 25 °C		-	2.8	-	Α	
	IRRM	T _J = 125 °C		-	6.5	-	A	
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	46	-	200	
		T _J = 125 °C		-	160	-	nC	

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER SYMBOL MIN. TYP. MAX. UNITS							
Maximum junction and storage temperature range	T _J , T _{Stg}	- 65	-	175	°C		
Thermal resistance, junction to case per diode	R_{thJC}	-	-	1.4	°C/W		
Marking device		Case style TO-220AB 30CTH03			ГН03		



Hyperfast Rectifier, 2 x 15 A FRED Pt® Vishay Semiconductors

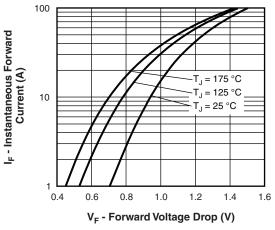


Fig. 1 - Typical Forward Voltage Drop Characteristics

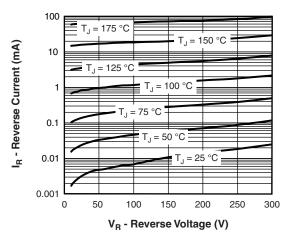


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

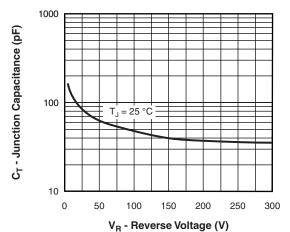


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

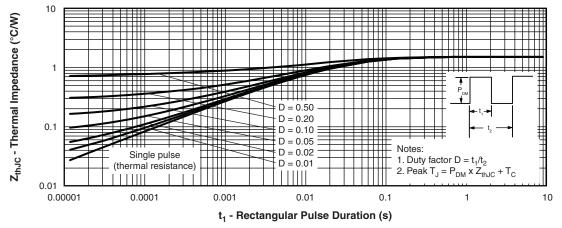


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

Vishay Semiconductors Hyperfast Rectifier, 2 x 15 A FRED Pt®



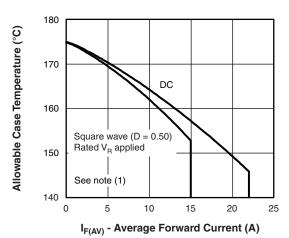
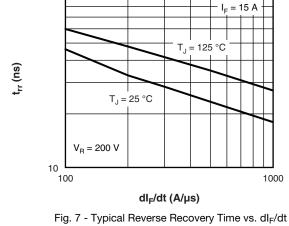


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current



100

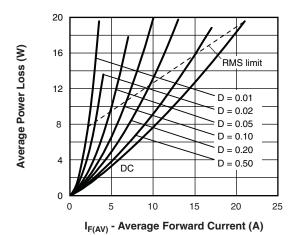


Fig. 6 - Forward Power Loss Characteristics

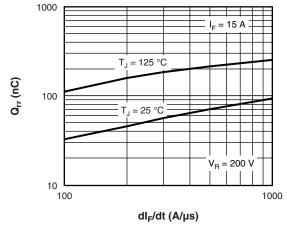


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{ll} \mbox{(1)} & \mbox{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \mbox{Forward power loss} = I_{F(AV)} \times V_{FM} \mbox{ at } (I_{F(AV)}/D) \mbox{ (see fig. 6)}; \\ \end{array}$ Pd_{REV} = Inverse power loss = $V_{R1} \times I_R (1 - D)$; I_R at V_{R1} = Rated V_R



Hyperfast Rectifier, 2 x 15 A FRED Pt® Vishay Semiconductors

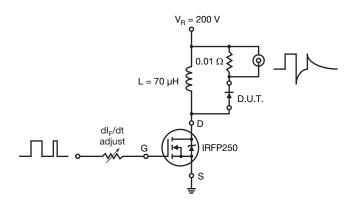
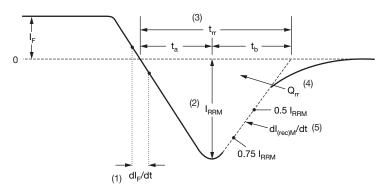


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) ${\rm Q_{rr}}$ area under curve defined by ${\rm t_{rr}}$ and ${\rm I_{RRM}}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

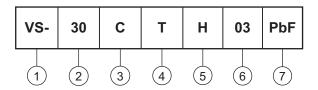
Fig. 10 - Reverse Recovery Waveform and Definitions

Vishay Semiconductors Hyperfast Rectifier, 2 x 15 A FRED Pt®



ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (30 = 30 A)

Circuit configuration:

C = Common cathode

4 - Package:

T = TO-220

5 - H = Hyperfast recovery

6 - Voltage rating (03 = 300 V)

7 - PbF = Lead (Pb)-free

Tube standard pack quantity: 50 pieces

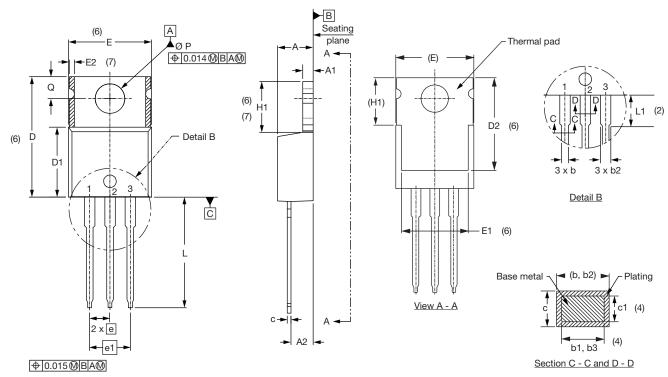
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95222</u>					
Part marking information	www.vishay.com/doc?95225				



Vishay Semiconductors

TO-220AB

DIMENSIONS in millimeters and inches



Lead assignments

Diodes

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIM	IETERS	INCHES		NOTES
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° t	o 93°	90° to 93°		
		•	•	•	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

Lead tip





Vishay

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